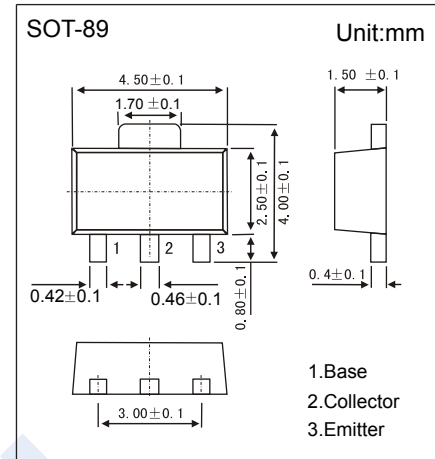


NPN Transistors

2SC4705

■ Features

- Collector Current Capability $I_C=0.2A$
- Collector Emitter Voltage $V_{CE0}=50V$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	60	V
Collector - Emitter Voltage	V_{CE0}	50	
Emitter - Base Voltage	V_{EB0}	15	
Collector Current - Continuous	I_C	200	mA
Collector Current - Pulse	I_{CP}	300	
Base Current	I_B	40	
Collector Power Dissipation (Note.1)	P_C	1.3	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 to 150	$^\circ C$

Note.1 : Mounted on ceramic substrate of $250mm^2 \times 0.8mm$

■ Electrical Characteristics $T_a = 25^\circ C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CB0}	$I_C = 100 \mu A, I_E = 0$	60			V
Collector- emitter breakdown voltage	V_{CE0}	$I_C = 1 mA, R_{BE} = \infty$	50			
Emitter - base breakdown voltage	V_{EB0}	$I_E = 100 \mu A, I_C = 0$	15			
Collector-base cut-off current	I_{CB0}	$V_{CB} = 40 V, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EB0}	$V_{EB} = 10 V, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 mA, I_B = 2 mA$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 100 mA, I_B = 2 mA$			1.2	
DC current gain	h_{FE}	$V_{CE} = 5 V, I_C = 100 mA$	800		3200	
Collector output capacitance	C_{ob}	$V_{CB} = 10 V, f = 1 MHz$		4		pF
Transition frequency	f_T	$V_{CE} = 10 V, I_C = 10 mA$		250		MHz

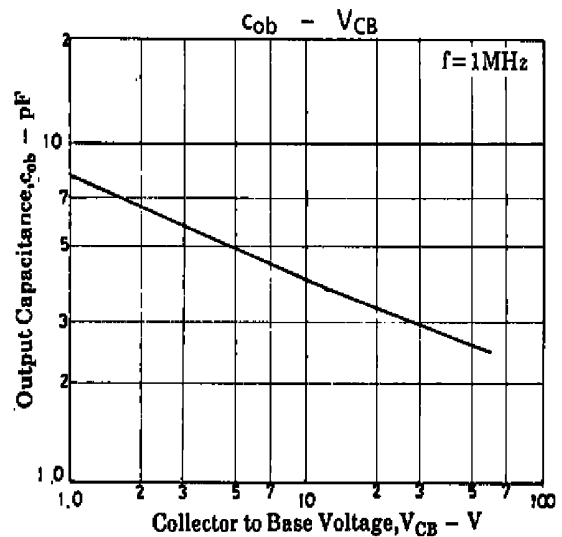
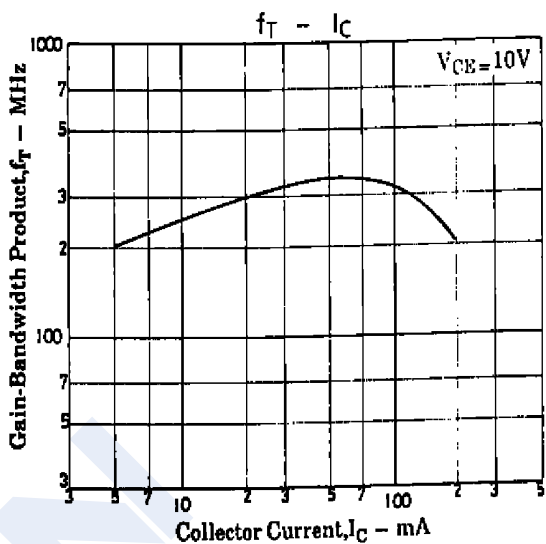
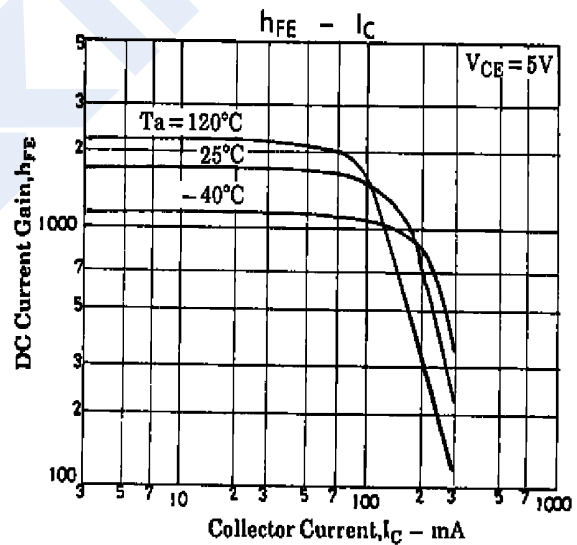
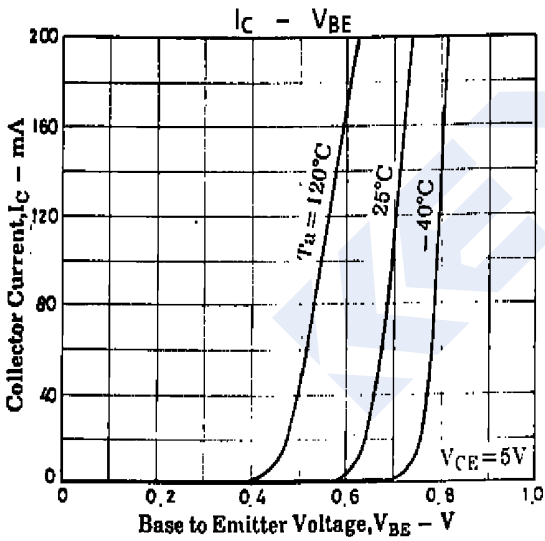
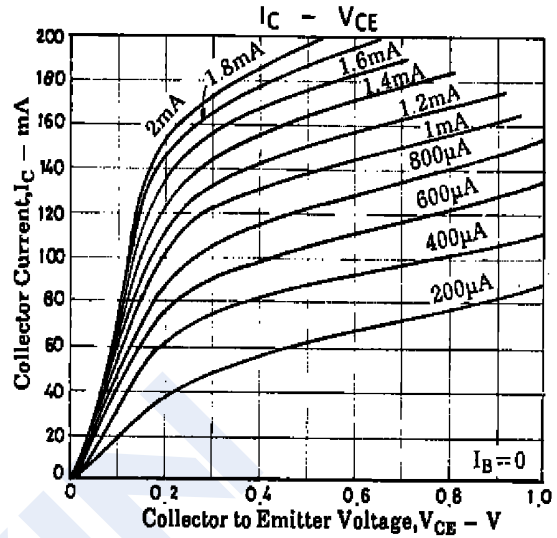
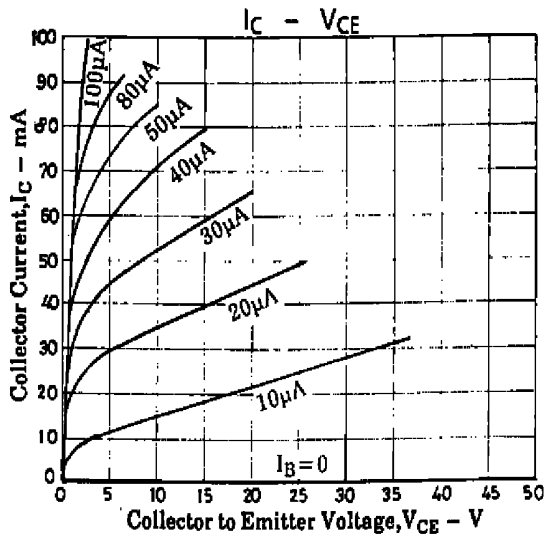
■ Marking

Marking	CP
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NPN Transistors

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■ Typical Characteristics



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■ Typical Characteristics

